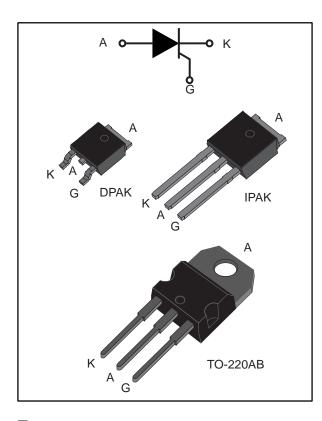


Sensitive 12 A SCRs

Datasheet - production data



Features

- On-state RMS current, I_{T(RMS)} 12 A
- Repetitive peak off-state voltage, V_{DRM}/V_{RRM} 600 V
- Triggering gate current, I_{GT} 200 μA
- ECOPACK®2 compliant component

Applications

- Capacitive ignition circuit for motorcycle engine
- DC brush motor drive for power tool or kitchen appliance
- Gas ignitor circuit
- Regulator driver for battery charger

Description

Thanks to highly sensitive triggering levels, the 12 A SCR series is suitable to fit all modes of control, found in applications such as overvoltage crowbar protection, motor control circuits in power tools and kitchen aids, inrush current limiting circuits, capacitive discharge ignition and voltage regulation circuits.

Available in through-hole or surface-mount packages, they provide an optimized performance in a limited space.

Table 1: Device summary

Order code	Order code V _{DRM} /V _{RRM} I _{GT}		Package
TS1220-600B		0.2 mA	DPAK
TS1220-600B-TR	COO \/	0.2 mA	DPAK
TS1220-600H	600 V	0.2 mA	IPAK
TS1220-600T		0.2 mA	TO-220AB

Characteristics TS1220

1 **Characteristics**

Table 2: Absolute ratings (limiting values)

Symbol	Parameter	Value	Unit		
I _{T(RMS)}	On-state RMS current (180° conduction angle)		T _c = 105 °C	12	Α
$I_{T(AV)}$	Average on-state current (180° conduction angle)		T _c = 105 °C	8	Α
1	Non repetitive surge peak	$t_p = 8.3 \text{ ms}$	T. 25 %C	115	Α
ITSM	on-state current t _p		T _j = 25 °C	110	A
l ² t	I^2t value for fusing $t_p = 10 \text{ ms}$		T _j = 25 °C	60	A ² s
dl/dt	Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$, $t_r \le 100 \text{ ns}$ $F = 60 \text{ Hz}$		T _j = 125 °C	50	A/µs
I _{GM}	Peak gate current $t_p = 20 \mu s$ $T_j = 125 °C$		T _j = 125 °C	4	Α
P _{G(AV)}	Average gate power dissipation	1	W		
T _{stg}	Storage junction temperature range	- 40 to + 150	°C		
Tj	Operating junction temperature range	- 40 to + 125			

Table 3: Sensitive electrical characteristics (Tj = 25 °C, unless otherwise specified)

Symbol	Test conditions						
lgт	V- 12 V D: 140 O		MAX.	200	μA		
V_{GT}	$V_D = 12 \text{ V}, \text{ R}_L = 140 \Omega$		MAX.	0.8	V		
V_{GD}	$V_D = V_{DRM}, R_L = 3.3\; k\Omega, R_{GK} = 220\; \Omega$	T _j = 125 °C	MIN.	0.1	V		
V_{RG}	$I_{RG} = 10 \mu A$	I _{RG} = 10 μA MIN. 8					
Ін	$I_T = 50 \text{ mA}, R_{GK} = 1 \text{ k}\Omega$ MAX. 5				mA		
lι	$I_G = 1 \text{ mA}, R_{GK} = 1 \text{ k}\Omega$ MAX.				mA		
dV/dt	$V_D = 67\% \ V_{DRM,} \ R_{GK} = 220 \ \Omega$	MIN.	5	V/µs			
V _{TM}	$I_{TM} = 24 \text{ A } t_p = 380 \mu\text{s}$	T _j = 25 °C	MAX.	1.6	V		
V_{t0}	Threshold voltage $T_j = 125 ^{\circ}\text{C}$		MAX.	0.85	V		
R_d	Dynamic resistance $T_j = 125 ^{\circ}\text{C}$		MAX.	30	mΩ		
I _{DRM}	V V P 1 kO	T _j = 25 °C	MAY	5	μA		
I _{RRM}	$V_{DRM} = V_{RRM}, R_{GK} = 1 k\Omega$	T _j = 125 °C	MAX.	2	mA		

Table 4: Thermal resistance

Symbol		Value	Unit		
R _{th(j-c)}	Junction to case (DC)		DPAK, IPAK, TO-220AB	1.3	°C/W
		$S = 0.5 \text{ cm}^{2(1)}$	DPAK	70	
R _{th(j-a)}	Junction to ambient (DC)		IPAK	100	°C/W
			TO-220AB	60	

Notes:

(1)S = Copper surface under tab

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TS1220 Characteristics

1.1 Characteristics (curves)

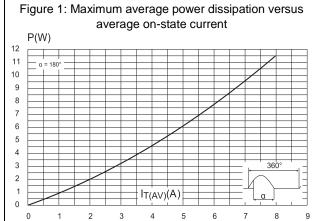


Figure 2: Average and DC on-state current versus case temperature

IT(AV)(A)

14

12

10

8

6

4

2

0

0

25

50

75

100

125

Figure 3: Average and DC on-state current versus ambient temperature (DPAK)

3.0 IT(AV)(A)

2.5 Device mounted on FR4 with recommended pad layout

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Figure 4: Relative variation of thermal impedance junction to case versus pulse duration

K=[Zth(j-c)/Rth(j-c)]

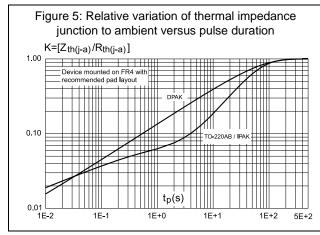
0.5

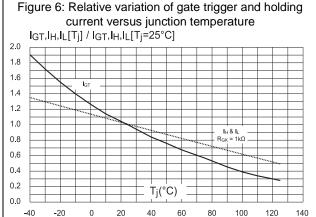
1E-3

1E-2

1E-1

1E+0





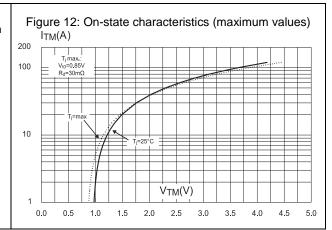
Characteristics TS1220

Figure 7: Relative variation of holding current versus gate-cathode resistance (typical values) $_{5.0}$ $\frac{I_H[R_{GK}] / I_H[R_{GK} = 1]}{I_H[R_{GK}]}$ 4.5 4.0 3.5 3.0 2.5 2.0 1.5 1.0 0.5 -R_{GK}(kΩ) 0.0 L 1E-2 1E-1 1E+0

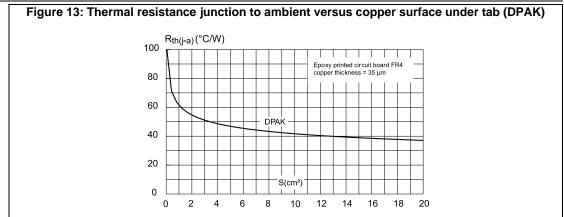
Figure 9: Relative variation of dV/dt immunity current versus gate-cathode capacitance (typical values) $4.0 \frac{\text{dV/dt}[C_{GK}] / \text{dV/dt}[R_{GK} = 220 \Omega]}{\text{dV/dt}[R_{GK} = 220 \Omega]}$ T_j = 125 °C V_D = 67% V_{DRM} R_{GK} = 220 Ω 3.5 3.0 2.5 20 1.5 1.0 0.5 CGK (nF) 0.0 25 50 100 125 150

Figure 10: Surge peak on-state current versus number of cycles

150 | TSM(A) | 140 | 130 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 | 140 |



TS1220 Characteristics





TS1220 Package information

2 **Package information**

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

Lead free lead plating; halogen free molding compound.

DPAK package mechanical data 2.1

Ε b4 c2 Γ 5 I E1 Α1

Figure 14: DPAK package outline

TS1220 Package information

Table 5: DPAK mechanical data

Dim	mm					
Dim.	Min.	Тур.	Max.	Min.	Тур.	Max.
А	2.18		2.40	0.0858		0.0945
A1	0.90		1.10	0.0354		0.0433
A2	0.03		0.23	0.0012		0.0091
b	0.64		0.90	0.0252		0.0354
b4	4.95		5.46	0.1949		0.2150
С	0.46		0.61	0.0181		0.0240
c2	0.46		0.60	0.0181		0.0240
D	5.97		6.22	0.2350		0.2449
D1	4.95		5.60	0.1949		0.2205
E	6.35		6.73	0.2500		0.2650
E1	4.32		5.50	0.1701		0.2165
е		2.286			0.0900	
e1	4.40		4.70	0.1732		0.1850
Н	9.35		10.40	0.3681		0.4094
L	1.00		1.78	0.0394		0.0701
L2			1.27			0.0500
L4	0.60		1.02	0.0236		0.0402
V2	-8°		8°	-8°		8°

Notes:

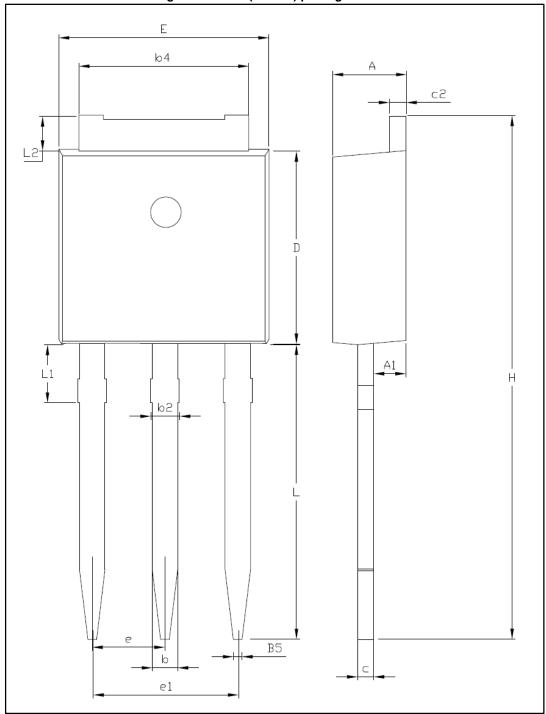
Figure 15: DPAK recommended footprint (dimensions are in mm)

⁽¹⁾Inch dimensions are for reference only.

Package information TS1220

2.2 IPAK package information

Figure 16: IPAK (TO-251) package outline



This package drawing may slightly differ from the physical package. However, all the specified dimensions are guaranteed.

TS1220 Package information

Table 6: IPAK (TO-251) package mechanical data

				imensions	Juli uulu	
Ref.		Millimiters			Inches ⁽¹⁾	
	Min.	Тур.	Max.	Min.	Тур.	Max.
Α	2.20		2.40	0.0866		0.0945
A1	0.90		1.10	0.0354		0.0433
b	0.64		0.90	0.0252		0.0354
b2			0.95			0.0374
b4	5.20		5.43	0.2047		0.2138
B5		0.30			0.0125	
С	0.45		0.60	0.0177		0.0236
c2	0.46		0.60	0.0181		0.0236
D	6.00		6.20	0.2362		0.2441
E	6.40		6.65	0.2520		0.2618
е		2.28			0.0898	
e1	4.40		4.60	0.1732		0.1811
Н		16.10			0.6339	
L	9.00		9.60	0.3545		0.3780
L1	0.80		1.20	0.0315		0.0472
L2		0.80	1.25		0.0315	0.0492
V1		10°			10°	

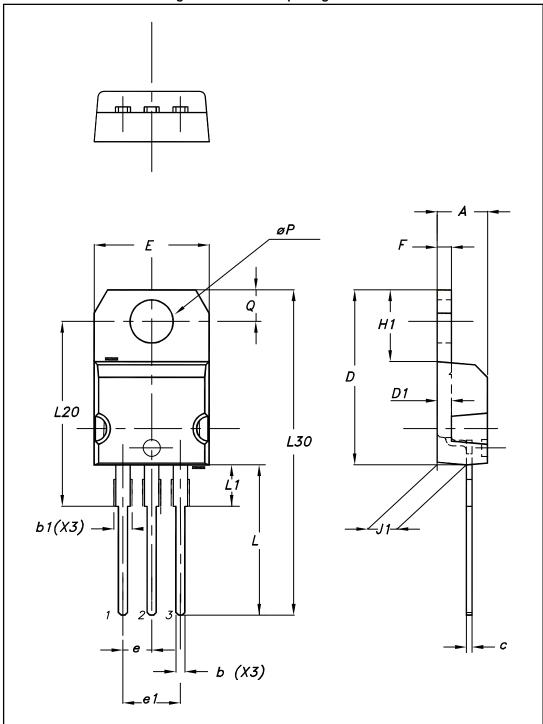
Notes:

 $^{^{(1)}}$ Inch dimensions are for reference only.

Package information TS1220

2.3 TO-220AB package information

Figure 17: TO-220AB package outline



TS1220 Package information

Table 7: TO-220AB package mechanical data

	Dimensions				
Ref.	Milli	meters	Inch	es ⁽¹⁾	
	Min.	Max.	Min.	Max.	
А	4.40	4.60	0.1732	0.1811	
b	0.61	0.88	0.0240	0.0346	
b1	1.14	1.70	0.0449	0.0669	
С	0.48	0.70	0.0189	0.0276	
D	15.25	15.75	0.6004	0.6201	
D1	1.2	7 typ.	0.0500 typ.		
Е	10.00	10.40	0.3937	0.4094	
е	2.40	2.70	0.0945	0.1063	
e1	4.95	5.15	0.1949	0.2028	
F	1.23	1.32	0.0484	0.0520	
H1	6.20	6.60	0.2441	0.2598	
J1	2.40	2.72	0.0945	0.1071	
L	13.00	14.00	0.5118	0.5512	
L1	3.50	3.93	0.1378	0.1547	
L20	16.40 typ.		0.6457 typ.		
L30	28.90 typ.		1.1378 typ.		
ØP	3.75	3.85	0.1476	0.1516	
Q	2.65	2.95	0.1043	0.1161	

Notes:



 $^{^{(1)}}$ Inch dimensions are for reference only.

Ordering information TS1220

3 Ordering information

Figure 18: TS1220 series

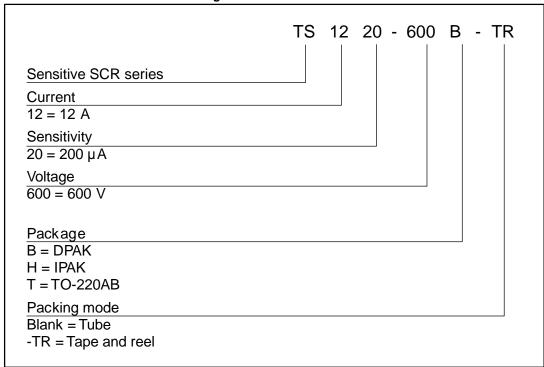


Table 8: Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
TS1220-600B	TS12 20600	DPAK	0.3 g	75	Tube
TS1220-600B-TR	TS12 20600	DPAK	0.3 g	2500	Tape and reel
TS1220-600H	TS12 20600	IPAK	0.3 g	75	Tube
TS1220-600T	TS1220600T	TO-220AB	2.3 g	50	Tube

TS1220 Revision history

4 Revision history

Table 9: Document revision history

Date	Revision	Changes		
08-Apr-2015	1	First issue.		
03-Aug-2016	2	Added section Applications and updated Features and in <i>Table 1:</i> "Device summary" in cover page. Updated Section 3: "Package information". Minor text changes.		

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